



INSULATED GATE BIPOLEAR TRANSISTOR

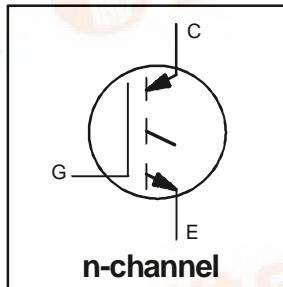
PD - 9.1138

IRGPH20S

Standard Speed IGBT

Features

- Switching-loss rating includes all "tail" losses
- Optimized for line frequency operation (to 400Hz)
- See Fig. 1 for Current vs. Frequency curve



$V_{CES} = 1200V$
$V_{CE(sat)} \leq 3.3V$
@ $V_{GE} = 15V, I_C = 6.6A$

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.

**Absolute Maximum Ratings**

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	10	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	6.6	
I_{CM}	Pulsed Collector Current ①	20	
I_{LM}	Clamped Inductive Load Current ②	20	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	5.0	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	2.1	°C/W
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{CES}}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{\text{GE}} = 0\text{V}$, $I_C = 250\mu\text{A}$
$V_{(\text{BR})\text{ECS}}$	Emitter-to-Collector Breakdown Voltage ④	20	—	—	V	$V_{\text{GE}} = 0\text{V}$, $I_C = 1.0\text{A}$
$\Delta V_{(\text{BR})\text{CES}/\Delta T_J}$	Temperature Coeff. of Breakdown Voltage	—	1.3	—	V/ $^\circ\text{C}$	$V_{\text{GE}} = 0\text{V}$, $I_C = 1.0\text{mA}$
$V_{\text{CE}(\text{on})}$	Collector-to-Emitter Saturation Voltage	—	2.2	3.3	V	$I_C = 6.6\text{A}$ $V_{\text{GE}} = 15\text{V}$
		—	2.9	—		$I_C = 10\text{A}$ See Fig. 2, 5
		—	2.9	—		$I_C = 6.6\text{A}$, $T_J = 150^\circ\text{C}$
		3.0	—	5.5		$V_{\text{CE}} = V_{\text{GE}}$, $I_C = 250\mu\text{A}$
$\Delta V_{\text{GE}(\text{th})/\Delta T_J}$	Temperature Coeff. of Threshold Voltage	—	-12	—	mV/ $^\circ\text{C}$	$V_{\text{CE}} = V_{\text{GE}}$, $I_C = 250\mu\text{A}$
g_{fe}	Forward Transconductance ⑤	1.5	3.0	—	S	$V_{\text{CE}} = 100\text{V}$, $I_C = 6.6\text{A}$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{\text{GE}} = 0\text{V}$, $V_{\text{CE}} = 1200\text{V}$
		—	—	1000		$V_{\text{GE}} = 0\text{V}$, $V_{\text{CE}} = 1200\text{V}$, $T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{\text{GE}} = \pm 20\text{V}$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	16	24	nC	$I_C = 6.6\text{A}$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	5.8	8.7		$V_{\text{CC}} = 400\text{V}$ See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	4.0	6.0		$V_{\text{GE}} = 15\text{V}$
$t_{d(\text{on})}$	Turn-On Delay Time	—	28	—	ns	$T_J = 25^\circ\text{C}$
t_r	Rise Time	—	32	—		$I_C = 6.6\text{A}$, $V_{\text{CC}} = 960\text{V}$
$t_{d(\text{off})}$	Turn-Off Delay Time	—	930	1400		$V_{\text{GE}} = 15\text{V}$, $R_G = 50\Omega$
t_f	Fall Time	—	850	1550		Energy losses include "tail"
E_{on}	Turn-On Switching Loss	—	0.57	—	mJ	See Fig. 9, 10, 11, 14
E_{off}	Turn-Off Switching Loss	—	5.4	—		
E_{ts}	Total Switching Loss	—	6.0	9.0		
$t_{d(\text{on})}$	Turn-On Delay Time	—	28	—	ns	$T_J = 150^\circ\text{C}$, $I_C = 6.6\text{A}$, $V_{\text{CC}} = 960\text{V}$
t_r	Rise Time	—	45	—		$V_{\text{GE}} = 15\text{V}$, $R_G = 50\Omega$
$t_{d(\text{off})}$	Turn-Off Delay Time	—	1100	—		Energy losses include "tail"
t_f	Fall Time	—	1800	—		See Fig. 10, 14
E_{ts}	Total Switching Loss	—	10	—	mJ	
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	360	—	pF	$V_{\text{GE}} = 0\text{V}$ $V_{\text{CC}} = 30\text{V}$ See Fig. 7 $f = 1.0\text{MHz}$
C_{oes}	Output Capacitance	—	24	—		
C_{res}	Reverse Transfer Capacitance	—	4.8	—		

Notes:

- ① Repetitive rating; $V_{\text{GE}}=20\text{V}$, pulse width limited by max. junction temperature.
(See fig. 13b)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ⑤ Pulse width $5.0\mu\text{s}$, single shot.
- ② $V_{\text{CC}}=80\%(V_{\text{CES}})$, $V_{\text{GE}}=20\text{V}$, $L=10\mu\text{H}$,
 $R_G=50\Omega$, (See fig. 13a)
- ④ Pulse width $\leq 80\mu\text{s}$; duty factor $\leq 0.1\%$.

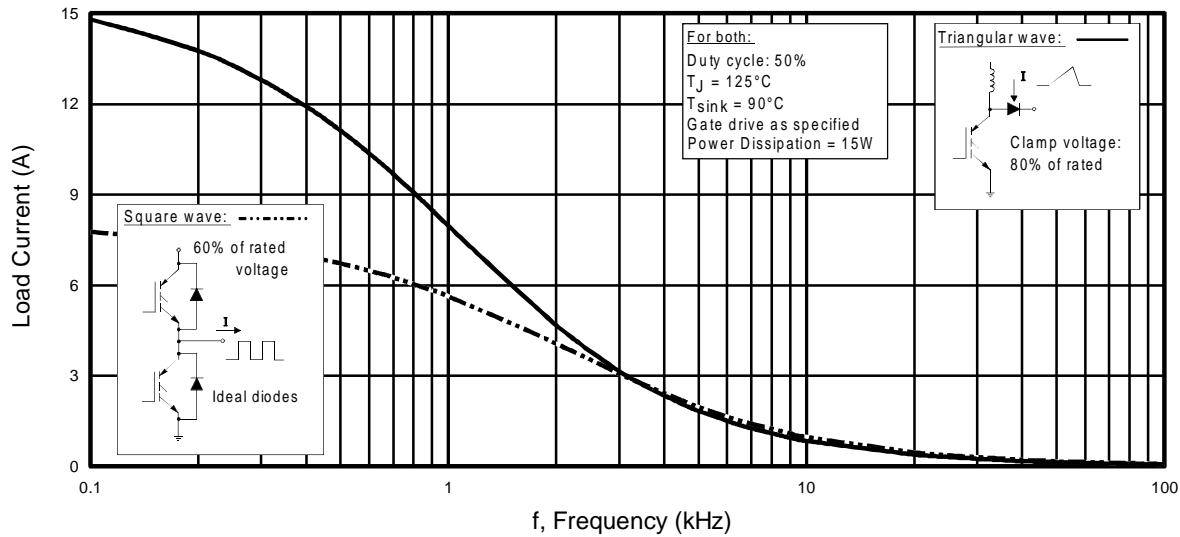


Fig. 1 - Typical Load Current vs. Frequency
 (For square wave, $I=I_{RMS}$ of fundamental; for triangular wave, $I=I_{PK}$)

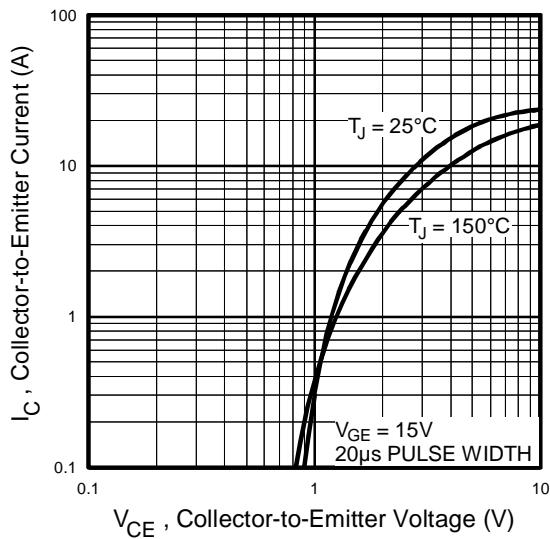


Fig. 2 - Typical Output Characteristics

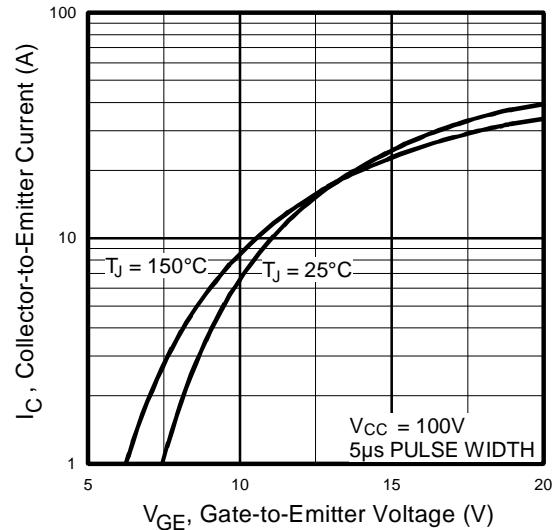


Fig. 3 - Typical Transfer Characteristics

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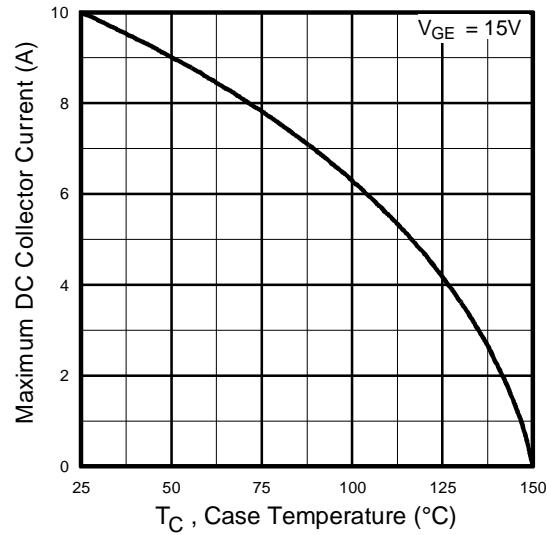


Fig. 4 - Maximum Collector Current vs. Case Temperature

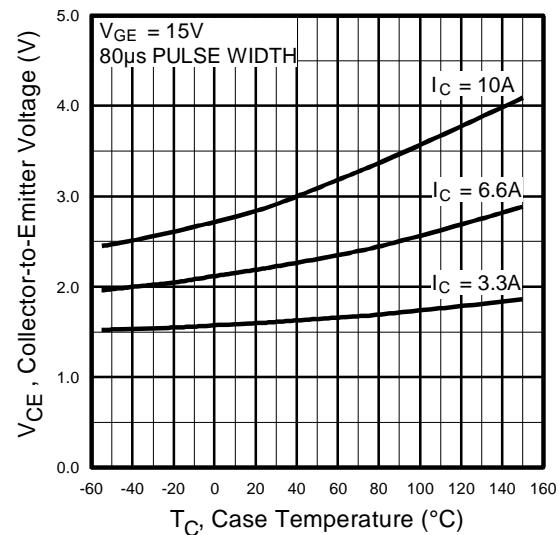


Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

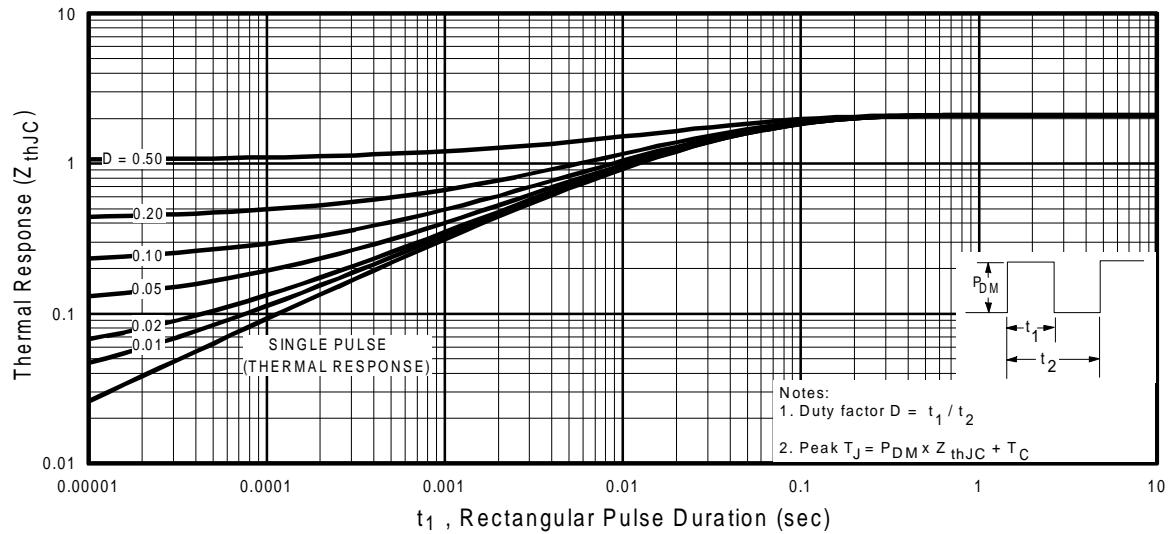


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

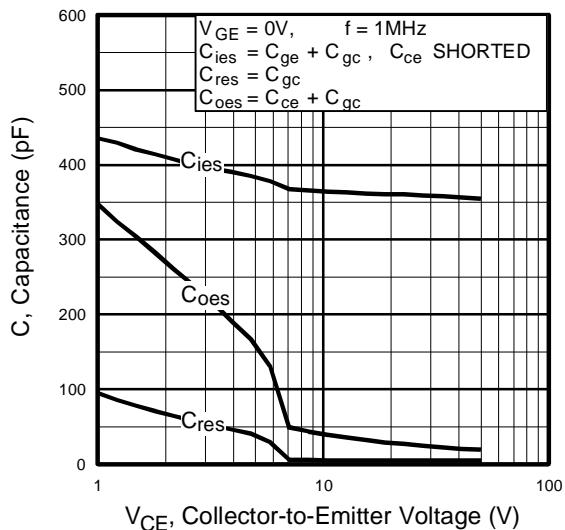


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

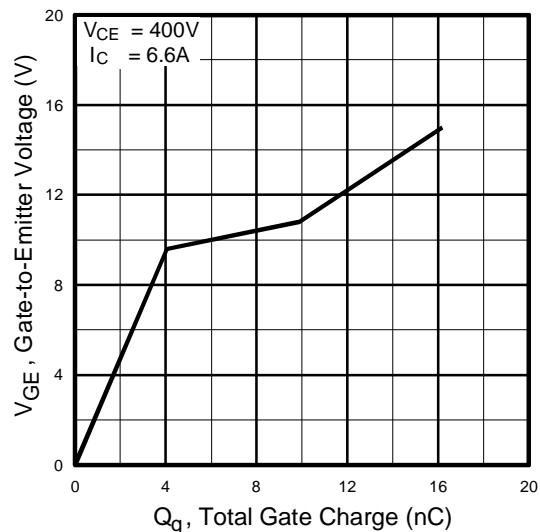


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

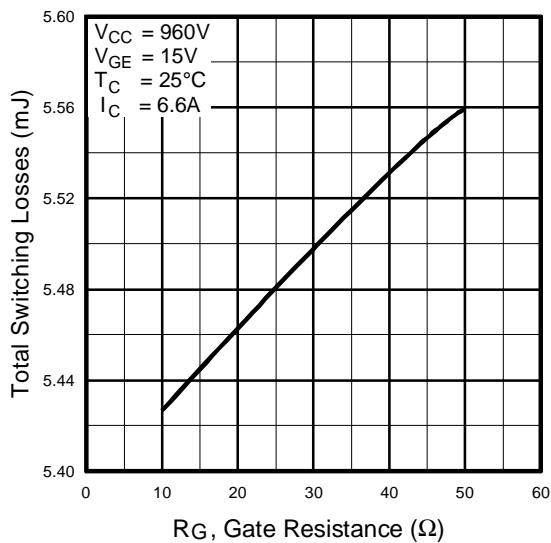


Fig. 9 - Typical Switching Losses vs. Gate Resistance

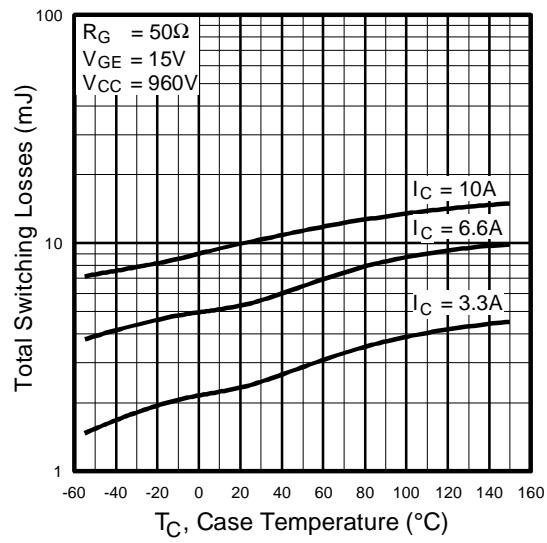


Fig. 10 - Typical Switching Losses vs. Case Temperature

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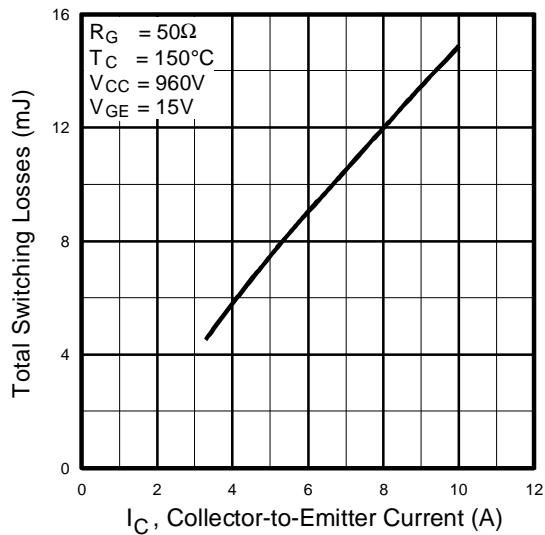


Fig. 11 - Typical Switching Losses vs.
Collector-to-Emitter Current

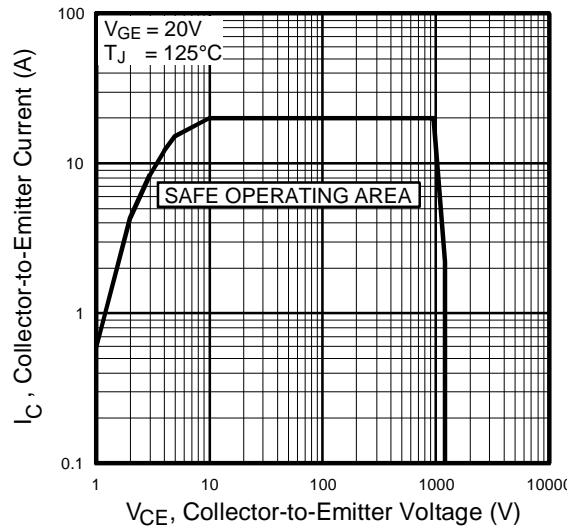


Fig. 12 - Turn-Off SOA

Refer to Section D for the following:

Appendix G: Section D - page D-9

- Fig. 13a - Clamped Inductive Load Test Circuit
- Fig. 13b - Pulsed Collector Current Test Circuit
- Fig. 14a - Switching Loss Test Circuit
- Fig. 14b - Switching Loss Waveform

Package Outline 3 - JEDEC Outline TO-247AC (TO-3P) **Section D - page D-13**